







TPS22992 ZHCSLK0A - JULY 2021 - REVISED DECEMBER 2021

具有可调上升时间的 TPS22992x 5V、8.7mΩ、6A 负载开关

1 特性

输入电压范围 (V_{IN}):

- TPS22992: 0.1V 至 5.5V - TPS22992S: 1V 至 5.5V • 偏置电压 (V_{BIAS}): 1.5V 至 5.5V

最大持续电流:6A

导通电阻 (R_{ON})8.7mΩ (典型值)

• 可调转换率控制

• 可调节快速输出放电 (QOD)

• 开漏电源正常 (PG) 信号

低功耗:

- 导通状态 (I_O): TPS22992 为 10μA (典型值) - 导通状态 (I_O): TPS22992S 为 30µA (典型值)

- 关闭状态 (I_{SD}): 0.1μA (典型值)

• 短路保护(仅限 TPS22992S)

热关断

• ON 引脚智能下拉电阻 (R_{PD ON})

- ON ≥ V_{IH} (I_{ON}): 25nA (典型值) - ON ≤ V_{IL} (R_{PD.ON}): 500kΩ (典型值)

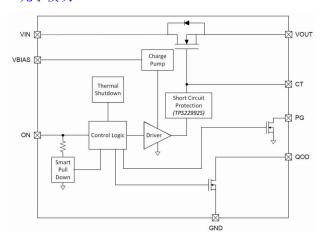
2 应用

• 数据存储

• PC 和笔记本电脑

工业 PC

光学模块



TPS22992x 方框图

3 说明

TPS22992x 产品系列包含两款器件: TPS22992 和 TPS22992S。每款器件都是采用 8.7mΩ 功率 MOSFET 的单通道负载开关,可在高达 5.5V 和 6A 的 应用中更大限度地提高功率密度。可配置的上升时间为 电源时序提供了灵活性,并更大限度地减小了高电容负 载的浪涌电流。

该开关由使能引脚 (ON) 控制,该引脚能够直接连接低 电压 GPIO 信号 (V_{IH} = 0.8V)。TPS22992x 器件具有 可选的 QOD 引脚,用于在开关关闭时快速输出放电, 并且输出的下降时间 (t_{FALI}) 可以通过外部电阻进行调 整。器件上有一个电源正常 (PG) 信号,指示主 MOSFET 何时完全导通,可用于启用下游负载。

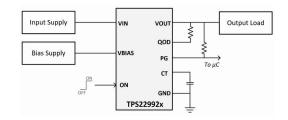
两款 TPS22992x 器件都具有热关断功能,以确保在高 温环境下提供保护。TPS22992S 器件还集成了过流保 护功能,可防止在操作或启动期间输出接地短路时损坏 器件。

对于小尺寸应用, TPS22992x 器件采用 1.25mm × 1.25mm、0.4mm 间距、8 引脚 WQFN 封装。当需要 更宽的引脚间距时, TPS22992 器件还提供 1.5mm × 1.25mm、0.5mm 间距、8 引脚 WQFN 封装。这两款 器件在自然通风环境下的额定运行温度范围为 - 40°C 至 +125°C。

器件信息

器件型号	封装 ⁽¹⁾	封装尺寸(标称值)
TPS22992	WQFN - 8 (RXP)	1.5mm x 1.25mm
TPS22992S	WQFN - 8 (RXN)	1.25mm x 1.25mm

如需了解所有可用封装,请参阅数据表末尾的可订购产品附



TPS2299x 电源时序应用



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4 Revision History 注:以前版本的页码可能与当前版本的页码不同

CI	hanges fro	m Revision	* (July	2021) to Re	vision A (December 2021)	Page
•	将状态从	"预告信息"	更改为	"量产数据"		1



5 Device Comparison Table

DEVICE	VIN RANGE	R _{ON} AT VBIAS = 5 V	QUIESCENT CURRENT	PACKAGE DIMENSIONS	PIN PITCH
TPS22992RXP	0.1 V to 5.5 V	8.7 mΩ	10 µA	1.5 mm x 1.25 mm	0.5 mm
TPS22992SRXN	1 V to 5.5 V	8.7 mΩ	40 μ A	1.25 mm x 1.25 mm	0.4 mm

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VBIAS

PG

6 Pin Configuration and Functions

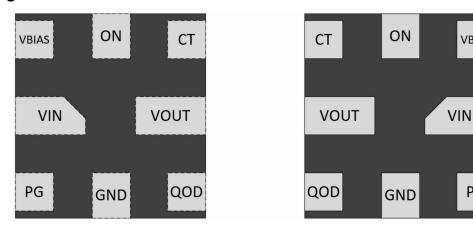


图 6-1. TPS22992x Pinout (Top View Left, Bottom View Right)

表 6-1. Pin Functions

PIN		I/O ⁽¹⁾	DESCRIPTION
NAME	NO.	1,0	DESCRIPTION
VBIAS	1	I	Bias voltage
VIN	2	I	Input voltage
PG	3	0	Open drain power good signal, asserted high when the output is full load ready
GND	4	_	Device ground
QOD	5	_	Quick output discharge pin
VOUT	6	0	Output voltage
СТ	7	0	Timing pin, can control the slew rate of the output through a capacitor to GND
ON	8	I	Enable pin

⁽¹⁾ I = Input, O = Output, I/O = Input or Output, G = Ground, P = Power.

7 Specifications

7.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

		MIN	MAX	UNIT
V _{IN}	Input Voltage	- 0.3	6	V
V _{BIAS}	Bias Voltage	- 0.3	6	V
V_{ON}, V_{PG}, V_{QOD}	Control Pin Voltage	- 0.3	6	V
V _{CT}	CT Pin Voltage		15	V
I _{MAX}	Maximum Current		6	Α
TJ	Junction temperature		Internally Limited	°C
T _{stg}	Storage temperature	- 65	150	°C

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Rating may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Condition. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

7.2 ESD Ratings

			VALUE	UNIT
V _(ESD) Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/ JEDEC JS-001 ⁽¹⁾	±2000	V	
	Electrostatic discriarge	Charged device model (CDM), per ANSI/ESDA/ JEDEC JS-002 ⁽²⁾	±1000	V

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

7.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM MAX	UNIT
V _{IN}	TPS22992 Input Voltage	0.1	V_{BIAS}	V
	TPS22992S Input Voltage	1	V_{BIAS}	V
V _{BIAS}	Bias Voltage	1.5	5.5	V
V _{IH}	ON Pin High Voltage Range	0.8	5.5	V
V _{IL}	ON Pin Low Voltage Range	0	0.35	V
V_{PG}, V_{QOD}	Control Pin Voltage	0	5.5	V
T _A	Ambient Temperature	- 40	125	°C

7.4 Thermal Information

		TPS2		
THERMAL METRIC (1)		RXP (WQFN)	RXN (WQFN)	UNIT
		8 PINS	8 PINS	
R ₀ JA	Junction-to-ambient thermal resistance	110.0	119.4	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	6.8	6.9	°C/W
Y_{JB}	Junction-to-board characterization parameter	36.6	35.2	°C/W

⁽¹⁾ For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.



7.5 Electrical Characteristics (VBIAS = 5 V)

Over operating free-air temperature range (unless otherwise noted). Typical values are at $T_A = 25$ °C and $V_{IN} = 5$ V.

	PARAMETER	TEST CONDITIONS	T _A	MIN	TYP	MAX	UNIT
Power 0	Consumption						
			25°C		0.1		uA
I _{SD,VBIA} s	VBIAS Shutdown Current	ON = 0 V	- 40°C to 85°C		,	0.25	uA
5			- 40°C to 125°C			0.36	uA
			25°C		10		uA
$I_{Q,VBIAS}$	VBIAS Quiescent Current (TPS22992)	ON > V _{IH}	- 40°C to 85°C			16	uA
	(11 022002)		- 40°C to 125°C			20	uA
			25°C		30		uA
$I_{Q,VBIAS}$	VBIAS Quiescent Current (TPS22992S)	ON > V _{IH}	- 40°C to 85°C		,	45	uA
	(======)		- 40°C to 125°C			50	uA
I _{SD,VIN}	VIN Shutdown Current	ON = 0 V	- 40°C to 125°C		0.1		uA
I _{ON}	ON pin leakage	ON = VBIAS	- 40°C to 125°C		0.1		uA
Perform	nance						
			25°C		8.7		mΩ
		VIN = 5 V	- 40°C to 85°C			12	mΩ
			- 40°C to 125°C			14	mΩ
		VIN = 3.3 V	25°C		8.7		mΩ
			- 40°C to 85°C		,	12	mΩ
	On-Resistance		- 40°C to 125°C			15	mΩ
			25°C		8.7		mΩ
R _{ON}		VIN = 1.8 V	- 40°C to 85°C			12	mΩ
			- 40°C to 125°C			14	mΩ
		VIN = 1.2 V	25°C		8.7		mΩ
			- 40°C to 85°C			12	mΩ
			- 40°C to 125°C			14	mΩ
		VIN = 0.8 V	25°C		8.7		mΩ
			- 40°C to 85°C			12	mΩ
			- 40°C to 125°C			14	mΩ
$V_{OL,PG}$	Power Good V _{OL}	I _{PG} = 1 mA	- 40°C to 125°C			0.2	V
_	0 (0 0	ON . W	25°C		500		kΩ
$R_{PD,ON}$	Smart Pull Down Resistance	ON < V _{IL}	- 40°C to 125°C			1000	kΩ
R _{QOD}	0000	ON . W	25°C		25		Ω
R _{QOD}	QOD Resistance	ON < V _{IL}	- 40°C to 125°C			100	Ω
Protecti	ion	-1					
I _{SC,H}	Short Circuit Current Limit (High)	$V_{OUT} \leqslant V_{IN}$ - 1.5 V	- 40°C to 125°C		11		Α
I _{SC,L}	Short Circuit Current Limit (Low)	$V_{OUT} \leqslant V_{SC}$	- 40°C to 125°C		1.5		Α
t _{SC}	Short Circuit Response Time	V _{IN} = 1 V to 5.5 V	- 40°C to 125°C		5		μS
	Object Circuit Data (1) The Asset	VOUT voltage level, rising	- 40°C to 125°C		0.45		V
V_{SC}	Short Circuit Detection Threshold	VOUT voltage level, falling	- 40°C to 125°C		0.35		V
TSD	Thermal Shutdown		-		170		°C
TSD _{HYS}	Thermal Shutdown Hysteresis		-		20		°C

Product Folder Links: TPS22992



7.6 Electrical Characteristics (VBIAS = 3.3 V)

over operating free-air temperature range (unless otherwise noted). Typical values are at $T_A = 25$ °C and $V_{IN} = 3.3$ V.

	PARAMETER	TEST CONDITIONS	T _A	MIN	TYP	MAX	UNIT
Power (Consumption						
			25°C		0.1		uA
I _{SD,VBIA}	VBIAS Shutdown Current	ON = 0 V	- 40°C to 85°C			0.2	uA
S			- 40°C to 125°C			0.27	uA
			25°C		10		uA
I _{Q,VBIAS}	VBIAS Quiescent Current (TPS22992)	ON > V _{IH}	- 40°C to 85°C			15	uA
	(17322992)		- 40°C to 125°C			16	uA
			25°C		26		uA
I _{Q,VBIAS}	VBIAS Quiescent Current (TPS22992S)	ON > V _{IH}	- 40°C to 85°C			42	uA
	(11 0229920)		- 40°C to 125°C			45	uA
I _{SD,VIN}	VIN Shutdown Current	ON = 0 V	- 40°C to 125°C		0.1		uA
I _{ON}	ON pin leakage	ON = VBIAS	- 40°C to 125°C		0.1		uA
Perform	nance						
			25°C		8.7		mΩ
		VIN = 3.3 V	- 40°C to 85°C		,	12	mΩ
	On-Resistance		- 40°C to 125°C			15	mΩ
		VIN = 1.8 V	25°C		8.7		mΩ
			- 40°C to 85°C			12	mΩ
			- 40°C to 125°C			15	mΩ
R _{ON}		VIN = 1.2 V	25°C		8.7		mΩ
			- 40°C to 85°C			12	mΩ
			- 40°C to 125°C			15	mΩ
		VIN = 0.8 V	25°C		8.7		m Ω
			- 40°C to 85°C		,	12	mΩ
			- 40°C to 125°C			15	mΩ
V _{OL,PG}	Power Good V _{OL}	I _{PG} = 1 mA	- 40°C to 125°C			0.2	V
			25°C		500		kΩ
$R_{PD,ON}$	Smart Pull Down Resistance	ON < V _{IL}	- 40°C to 125°C			1000	kΩ
			25°C		25		Ω
R_{QOD}	QOD Resistance	ON < V _{IL}	- 40°C to 125°C			100	Ω
Protecti	on						
I _{SC,H}	Short Circuit Current Limit (High)	$V_{OUT} \le V_{IN}$ - 1.5 V	- 40°C to 125°C		10		Α
I _{SC,L}	Short Circuit Current Limit (Low)	V _{OUT} ≤ V _{SC}	- 40°C to 125°C		1.5		Α
t _{SC}	Short Circuit Response Time	V _{IN} = 1 V to 5.5 V	- 40°C to 125°C		5		μs
	·	VOUT voltage level, rising	- 40°C to 125°C		0.45		V
V_{SC}	Short Circuit Detection Threshold	VOUT voltage level, falling	- 40°C to 125°C		0.35		V
TSD	Thermal Shutdown		-		170		°C
TSD _{HYS}			_		20		°C

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7.7 Electrical Characteristics (VBIAS = 1.5 V)

Over operating free-air temperature range (unless otherwise noted). Typical values are at $T_A = 25^{\circ}C$ and $V_{IN} = 1.5V$.

	PARAMETER	TEST CONDITIONS	T _A	MIN TYP	MAX	UNIT
Power 0	Consumption					
			25°C	0.1		uA
I _{SD,VBIA} S	D,VBIA VBIAS Shutdown Current	ON = 0 V	- 40°C to 85°C		0.2	uA
3			- 40°C to 125°C		0.25	uA
			25°C	8		uA
I _{Q,VBIAS}	VBIAS Quiescent Current (TPS22992)	ON > V _{IH}	- 40°C to 85°C		12	uA
	(- 40°C to 125°C		14	uA
			25°C	22		uA
$I_{Q,VBIAS}$	VBIAS Quiescent Current (TPS22992S)	ON > V _{IH}	- 40°C to 85°C		29	uA
			- 40°C to 125°C		31	uA
$I_{SD,VIN}$	VIN Shutdown Current	ON = 0 V	- 40°C to 125°C	0.1		uA
I _{ON}	ON pin leakage	ON = VBIAS	- 40°C to 125°C	0.1		uA
Perform	nance					
		VIN = 1.5 V	25°C	12.7		$\boldsymbol{m}\Omega$
	On-Resistance		- 40°C to 85°C		21	$\mathbf{m}\Omega$
			- 40°C to 125°C		27	$\mathbf{m}\Omega$
		VIN = 1.2 V	25°C	11.2		mΩ
R _{ON}			- 40°C to 85°C		18	mΩ
			- 40°C to 125°C		25	$\mathbf{m}\Omega$
		VIN = 0.8 V	25°C	10		mΩ
			- 40°C to 85°C		16	mΩ
			- 40°C to 125°C		23	$\mathbf{m}\Omega$
$V_{OL,PG}$	Power Good V _{OL}	I _{PG} = 1 mA	- 40°C to 125°C		0.2	V
_	Consent Dull Design Designation	ON 41/	25°C	500		kΩ
$R_{PD,ON}$	Smart Pull Down Resistance	ON < V _{IL}	- 40°C to 125°C		1000	$\mathbf{k} \Omega$
ם	OOD Decistance	ON a V	25°C	25		Ω
R_{QOD}	QOD Resistance	ON < V _{IL}	- 40°C to 125°C		100	Ω
Protecti	on					
I _{SC,H}	Short Circuit Current Limit (High)	$V_{OUT} \leqslant V_{IN}$ - 1.5 V	- 40°C to 125°C	10		Α
I _{SC,L}	Short Circuit Current Limit (Low)	$V_{OUT} \leqslant V_{SC}$	- 40°C to 125°C	1.5		Α
t _{SC}	Short Circuit Response Time	V _{IN} = 1 V to 5.5 V	- 40°C to 125°C	5		μ s
\/	Short Circuit Dotoction Throat-1-1	VOUT voltage level, rising	- 40°C to 125°C	0.45		V
V_{SC}	Short Circuit Detection Threshold	VOUT voltage level, falling	- 40°C to 125°C	0.35		V
TSD	Thermal Shutdown		-	170		°C
TSD _{HYS}	Thermal Shutdown Hysteresis		-	20		°C

7.8 Switching Characteristics (VBIAS = 5 V)

Over operating free-air temperature range (unless otherwise noted). Typical values are at $T_A = 25$ °C.

	PARAMETER	 TEST CONDITIONS	MIN	TYP	MAX	UNIT
VIN = 5V				,		
t _{ON}	Turn ON time	R_L = 10 Ω , C_L = 10 uF, CT = 1000 pF		1980		us
t _{RISE}	Rise time	R_L = 10 Ω , C_L = 10 uF, CT = 1000 pF		1430		us

7.8 Switching Characteristics (VBIAS = 5 V) (continued)

Over operating free-air temperature range (unless otherwise noted). Typical values are at $T_A = 25$ °C.

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _D	Delay time	R_L = 10 Ω , C_L = 10 uF, CT = 1000 pF		554		us
t _{FALL}	Fall time	R_L = 10 Ω , C_L = 10 uF, CT = 1000 pF		224		us
t _{OFF}	Turn OFF time	R_L = 10 Ω , C_L = 10 uF, CT = 1000 pF		15.3		us
VIN = 3	3.3V				l	
t _{ON}	Turn ON time	R_L = 10 Ω , C_L = 10 uF, CT = 1000 pF		1480		us
t _{RISE}	Rise time	R_L = 10 Ω , C_L = 10 uF, CT = 1000 pF		962		us
t _D	Delay time	R_L = 10 Ω , C_L = 10 uF, CT = 1000 pF		517		us
t _{FALL}	Fall time	R_L = 10 Ω , C_L = 10 uF, CT = 1000 pF		218		us
t _{OFF}	Turn OFF time	R_L = 10 Ω , C_L = 10 uF, CT = 1000 pF		14.8		us
VIN = 1	.8V				'	
t _{ON}	Turn ON time	R_L = 10 Ω , C_L = 10 uF, CT = 1000 pF		1040		us
t _{RISE}	Rise time	R_L = 10 Ω , C_L = 10 uF, CT = 1000 pF		553		us
t _D	Delay time	R_L = 10 Ω , C_L = 10 uF, CT = 1000 pF		489		us
t _{FALL}	Fall time	R_L = 10 Ω , C_L = 10 uF, CT = 1000 pF		220		us
t _{OFF}	Turn OFF time	R_L = 10 Ω , C_L = 10 uF, CT = 1000 pF		15.2		us
VIN = 1	.2V				'	
t _{ON}	Turn ON time	R_L = 10 Ω , C_L = 10 uF, CT = 1000 pF		862		us
t _{RISE}	Rise time	R_L = 10 Ω , C_L = 10 uF, CT = 1000 pF		386		us
t _D	Delay time	$R_L = 10 \Omega$, $C_L = 10 uF$, $CT = 1000 pF$		476		us
t _{FALL}	Fall time	R_L = 10 Ω , C_L = 10 uF, CT = 1000 pF		221		us
t _{OFF}	Turn OFF time	R_L = 10 Ω , C_L = 10 uF, CT = 1000 pF		15.5		us
VIN = 0	0.8V					
t _{ON}	Turn ON time	R_L = 10 Ω , C_L = 10 uF, CT = 1000 pF		743		us
t _{RISE}	Rise time	R_L = 10 Ω , C_L = 10 uF, CT = 1000 pF		282		us
t _D	Delay time	R_L = 10 Ω , C_L = 10 uF, CT = 1000 pF		462		us
t _{FALL}	Fall time	R_L = 10 Ω , C_L = 10 uF, CT = 1000 pF		222		us
t _{OFF}	Turn OFF time	$R_L = 10 \Omega$, $C_L = 10 uF$, $CT = 1000 pF$		16.4		us

7.9 Switching Characteristics (VBIAS = 3.3 V)

Over operating free-air temperature range (unless otherwise noted). Typical values are at TA = 25°C.

	PARAMETER	TEST CONDITIONS	MIN TYP MA	X UNIT
VIN = 3	.3V			<u> </u>
t _{ON}	Turn ON time	R_L = 10 Ω , C_L = 10 uF, CT = 1000 pF	1560	us
t _{RISE}	Rise time	R_L = 10 Ω , C_L = 10 uF, CT = 1000 pF	1010	us
t _D	Delay time	R_L = 10 Ω , C_L = 10 uF, CT = 1000 pF	547	us
t _{FALL}	Fall time	R_L = 10 Ω , C_L = 10 uF, CT = 1000 pF	224	us
t _{OFF}	Turn OFF time	R_L = 10 Ω , C_L = 10 uF, CT = 1000 pF	14.1	us
VIN = 1	.8V			
t _{ON}	Turn ON time	R_L = 10 Ω , C_L = 10 uF, CT = 1000 pF	1090	us
t _{RISE}	Rise time	R_L = 10 Ω , C_L = 10 uF, CT = 1000 pF	581	us
t _D	Delay time	R_L = 10 Ω , C_L = 10 uF, CT = 1000 pF	505	us
t _{FALL}	Fall time	R_L = 10 Ω , C_L = 10 uF, CT = 1000 pF	223	us

7.9 Switching Characteristics (VBIAS = 3.3 V) (continued)

Over operating free-air temperature range (unless otherwise noted). Typical values are at TA = 25°C.

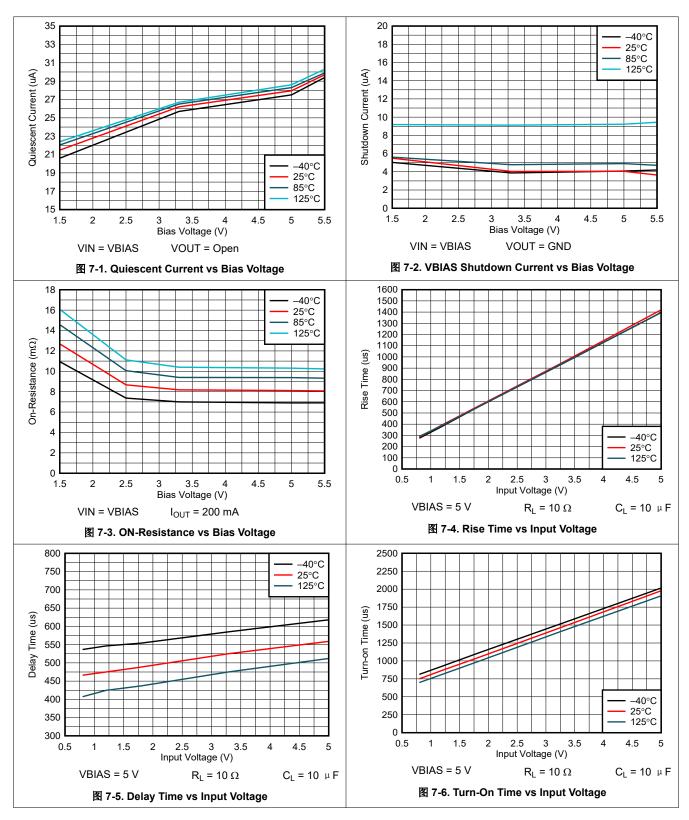
	PARAMETER	TEST CONDITIONS	MIN TYP MAX	UNIT
t _{OFF}	Turn OFF time	R_L = 10 Ω , C_L = 10 uF, CT = 1000 pF	15.1	us
VIN = 1	.2V			
t _{ON}	Turn ON time	R_L = 10 Ω , C_L = 10 uF, CT = 1000 pF	903	us
t _{RISE}	Rise time	R_L = 10 Ω , C_L = 10 uF, CT = 1000 pF	406	us
t _D	Delay time	R_L = 10 Ω , C_L = 10 uF, CT = 1000 pF	498	us
t _{FALL}	Fall time	R_L = 10 Ω , C_L = 10 uF, CT = 1000 pF	223	us
t _{OFF}	Turn OFF time	R_L = 10 Ω , C_L = 10 uF, CT = 1000 pF	15.3	us
VIN = 0	.8V			
t _{ON}	Turn ON time	R_L = 10 Ω , C_L = 10 uF, CT = 1000 pF	774	us
t _{RISE}	Rise time	R_L = 10 Ω , C_L = 10 uF, CT = 1000 pF	284	us
t _D	Delay time	R_L = 10 Ω , C_L = 10 uF, CT = 1000 pF	489	us
t _{FALL}	Fall time	R_L = 10 Ω , C_L = 10 uF, CT = 1000 pF	222	us
t _{OFF}	Turn OFF time	R_L = 10 Ω , C_L = 10 uF, CT = 1000 pF	15.1	us

7.10 Switching Characteristics (VBIAS = 1.5 V)

Over operating free-air temperature range (unless otherwise noted). Typical values are at TA = 25°C.

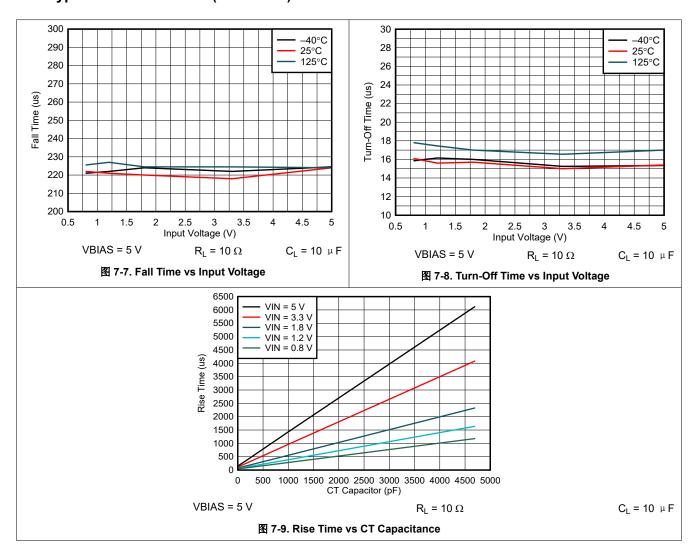
	PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
VIN = 1	.5V				
t _{ON}	Turn ON time	$R_L = 10 \Omega$, $C_L = 10 uF$, $CT = 1000 pF$	1040		us
t _{RISE}	Rise time	R_L = 10 Ω , C_L = 10 uF, CT = 1000 pF	501		us
t _D	Delay time	R_L = 10 Ω , C_L = 10 uF, CT = 1000 pF	542		us
t _{FALL}	Fall time	$R_L = 10 \Omega$, $C_L = 10 uF$, $CT = 1000 pF$	225		us
t _{OFF}	Turn OFF time	R_L = 10 Ω , C_L = 10 uF, CT = 1000 pF	13.4		us
VIN = 1	.2V				
t _{ON}	Turn ON time	R_L = 10 Ω , C_L = 10 uF, CT = 1000 pF	959		us
t _{RISE}	Rise time	R_L = 10 Ω , C_L = 10 uF, CT = 1000 pF	421		us
t _D	Delay time	R_L = 10 Ω , C_L = 10 uF, CT = 1000 pF	538		us
t _{FALL}	Fall time	R_L = 10 Ω , C_L = 10 uF, CT = 1000 pF	221		us
t _{OFF}	Turn OFF time	$R_L = 10 \Omega$, $C_L = 10 uF$, $CT = 1000 pF$	13.9		us
VIN = 0).8V			'	
t _{ON}	Turn ON time	$R_L = 10 \Omega$, $C_L = 10 uF$, $CT = 1000 pF$	840		us
t _{RISE}	Rise time	$R_L = 10 \Omega$, $C_L = 10 uF$, $CT = 1000 pF$	314		us
t _D	Delay time	R_L = 10 Ω , C_L = 10 uF, CT = 1000 pF	526		us
t _{FALL}	Fall time	R_L = 10 Ω , C_L = 10 uF, CT = 1000 pF	218		us
t _{OFF}	Turn OFF time	$R_L = 10 \Omega$, $C_L = 10 uF$, $CT = 1000 pF$	14.8		us

7.11 Typical Characteristics





7.11 Typical Characteristics (continued)



8 Timing Diagram

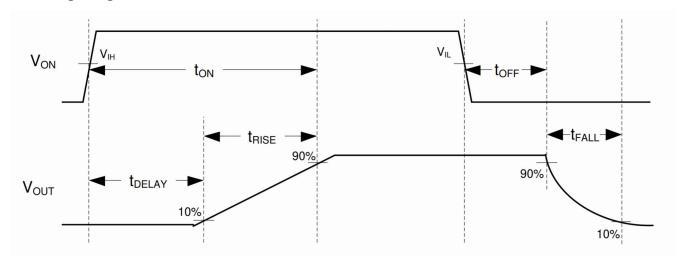


图 8-1. TPS22992x Timing Parameters



9 Detailed Description

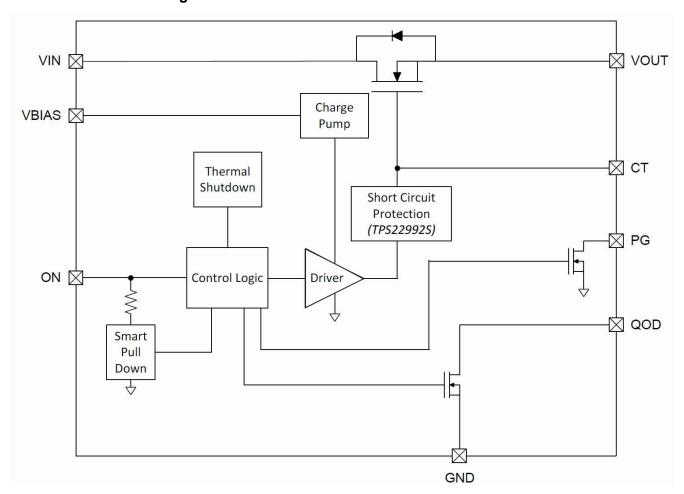
9.1 Overview

The TPS22992 and TPS22992S devices are both single-channel load switches with an $8.7\text{-m}\Omega$ power MOSFET designed to operate up to 6 A. The voltage range of the TPS22992 device is 0.1 V to 5.5 V, and the voltage range of the TPS22992S device is 1 V to 5.5 V. A configurable rise time provides flexibility for power sequencing and minimizes inrush current for high capacitance loads.

The switch is controlled by an enable pin (ON), which is capable of interfacing directly with low voltage GPIO signals down to its V_{IH} level of 0.8 V. The TPS22992x device has an optional QOD pin for quick output discharge when switch is turned off, and the fall time (t_{FALL}) of the output can be adjusted through an external resistor. There is a Power Good (PG) signal on the device that indicates when the main MOSFET is fully turned on and the on-resistance is at its final value.

Both TPS22992x devices come with thermal shutdown to ensure protection in high temperature environments. The TPS22992S also integrates overcurrent protection, preventing damage to the device if the output is shorted to ground during operation or start-up.

9.2 Functional Block Diagram



9.3 Feature Description

9.3.1 ON and OFF Control

The ON pin controls the state of the switch. The ON pin is compatible with standard GPIO logic threshold so it can be used in a wide variety of applications. When power is first applied to VIN, a Smart Pulldown is used to keep the ON pin from floating until the system sequencing is complete. After the ON pin is deliberately driven high (\geqslant VIH), the Smart Pulldown is disconnected to prevent unnecessary power loss. See the below table when the ON Pin Smart Pulldown is active.

ON Pin Voltage	ON Pin Function
≤ V _{IL}	Pulldown active
≥ V _{IH}	No pulldown

9.3.2 Adjustable Quick Output Discharge

The TPS22992x device includes a QOD feature that can be configured in one of three ways:

- QOD pin shorted to VOUT pin. Using this method, the discharge rate after the switch becomes disabled is controlled with the value of the internal resistance RQOD. The value of this resistance is listed in the Electrical Characteristics table.
- QOD pin connected to VOUT pin using an external resistor REXT. After the switch becomes disabled, the discharge rate is controlled by the value of the total resistance of the QOD.
- QOD pin is unused and left floating. Using this method, there is no quick output discharge functionality, and the output remains floating after the switch is disabled.

Fall time is dependent on the strength of the configured pulldown resistance on the output.

9.3.3 Adjustable Slew Rate

A capacitor to GND on the CT pin sets the slew rate, and the higher the capacitance the lower the slew rate. The voltage on the CT pin can be as high as 15 V; therefore, the minimum voltage rating for the CT capacitor must be 30 V for optimal performance. Rise times for VBIAS = 5 V are shown below.

CT Capacitor	VIN = 5 V	VIN = 3.3 V	VIN = 1.8 V	VIN = 1.2 V	VIN = 0.8 V
0 pF	147 µs	113 µs	77 µs	59 µs	45 µs
220 pF	426 µs	297 µs	179 µs	129 µs	94 µs
1000 pF	1430 µs	962 µs	553 µs	386 µs	282 µs
4700 pF	6130 µs	4090 µs	2330 µs	1640 µs	1180 µs

The following equation can be used to estimate the rise time for different VIN and CT capacitors at VBIAS = 5 V.

$$t_R = V_{IN} \times (0.27 \times CT + 25.5) + 24.9$$
 (1)

Where:

- t_R = Rise time in μs
- V_{IN} = Input voltage in V
- CT = CT capacitance in pF

9.3.4 Power Good (PG) Signal

The TPS22992x device has a Power Good (PG) output signal to indicate the gate of the pass FET is driven high and the switch is on with the on-resistance close to its final value (full load ready). The signal is an active high and open drain output which can be connected to a voltage source through an external pullup resistor, R_{PU}. This voltage source can be VOUT from the TPS22992x device or another external voltage. VBIAS is required for PG to have a valid output.

9.3.5 Thermal Shutdown

When the device temperature reaches 170°C (typical), the device shuts itself off to prevent thermal damage. After the device cools off by about 20°C, it turns back on. If the device is kept in a thermally stressful environment, then the device oscillates between these two states until it can keep its temperature below the thermal shutdown point.

9.3.6 Short Circuit Protection (TPS22992S)

The device limits current to the output in case of output shorts. When a short occurs, the large VIN to VOUT voltage drop causes the switch to limit the output current (ISC). When the output is below the short circuit threshold (VSC), a lower limit is used to minimize the power dissipation while the fault is present. The device continues to limit the current until it reaches its thermal shutdown temperature. At this time, the device turns off until its temperature has lowered by the thermal hysteresis (20°C typical) before turning on again.

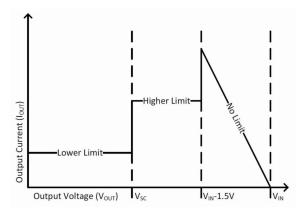


图 9-1. Output Short Circuit Current Limiting

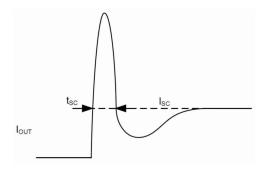


图 9-2. Output Short Circuit Response

9.4 Device Functional Modes

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The below table summarizes the device functional modes.

ON	Fault Condition	VOUT State
L	N/A	Hi-Z
Н	None	V _{IN} (through R _{ON})
Н	Output short	Current limited (TPS22992S)
X	Thermal shutdown	Hi-Z

10 Application and Implementation

备注

以下应用部分中的信息不属于 TI 器件规格的范围, TI 不担保其准确性和完整性。TI 的客户应负责确定器件是否适用于其应用。客户应验证并测试其设计,以确保系统功能。

10.1 Application Information

This section highlights some of the design considerations when implementing this device in various applications.

10.2 Typical Application

This typical application demonstrates how the TPS22992x device can be used to limit start-up inrush current.

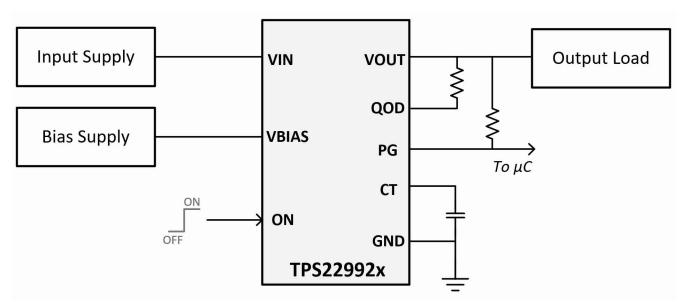


图 10-1. TPS22992x Typical Application

10.2.1 Design Requirements

For this example, the values below are used as the design parameters.

 PARAMETER
 VALUE

 V_{BIAS}
 5 V

 V_{IN}
 5 V

 C_L
 47 uF

 Maximum acceptable inrush current
 200 mA

表 10-1. Design Parameters

10.2.2 Detailed Design Procedure

When the switch is enabled, the output capacitance must be charged up from 0 V to the set value (5 V in this example). This charge arrives in the form of inrush current. Inrush current can be calculated using the equation below.

Inrush Current =
$$C_L \times dVOUT/dt$$
 (2)

Where:



- C₁ is the output capacitance.
- dVOUT is the change in VOUT during the ramp up of the output voltage when device is enabled.
- dt is the rise time in VOUT during the ramp up of the output voltage when the device is enabled.

The TPS22992 offers an adjustable rise time for VOUT, allowing the user to control the inrush current during turn-on. The appropriate rise time can be calculated using the design requirements and the inrush current equation as shown below.

$$200 \text{ mA} = 47 \mu\text{F} \times 5 \text{ V/dt}$$
 (3)

$$dt = 1175 \,\mu s$$
 (4)

To ensure an inrush current of less than 200 mA, a C_T value that yields a rise time of more than 1175 μ s must be chosen. See the oscilloscope captures in the Application Performance Plots section for an example of how the C_T capacitor can be used to reduce inrush current.

10.2.3 Application Performance Plots

The below oscilloscope captures show the difference between the inrush current for $C_T = 0$ pF and $C_T = 1000$ pF settings. The $C_T = 1000$ pF setting is able to keep the inrush current under the required 200 mA, while the $C_T = 0$ pF setting is too fast for this design.

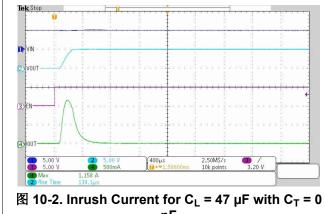


图 10-3. Inrush Current for $C_L = 47 \mu F$ with $C_T =$ 1000 pF



11 Power Supply Recommendations

The TPS22992 device is designed to operate with a VIN range of 0.1 V to 5.5 V, and the TPS22992S device over a range of 1 V to 5.5 V. The VIN power supply must be well regulated and placed as close to the device terminal as possible. The power supply must be able to withstand all transient load current steps. In most situations, using an input capacitance (C_{IN}) of 1 μ F is sufficient to prevent the supply voltage from dipping when the switch is turned on. In cases where the power supply is slow to respond to a large transient current or large load current step, additional bulk capacitance can be required on the input.

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12 Layout

12.1 Layout Guidelines

For best performance, all traces must be as short as possible. To be most effective, the input and output capacitors must be placed close to the device to minimize the effects that parasitic trace inductances can have on normal operation. Using wide traces for VIN, VOUT, and GND helps minimize the parasitic electrical effects.

12.2 Layout Example

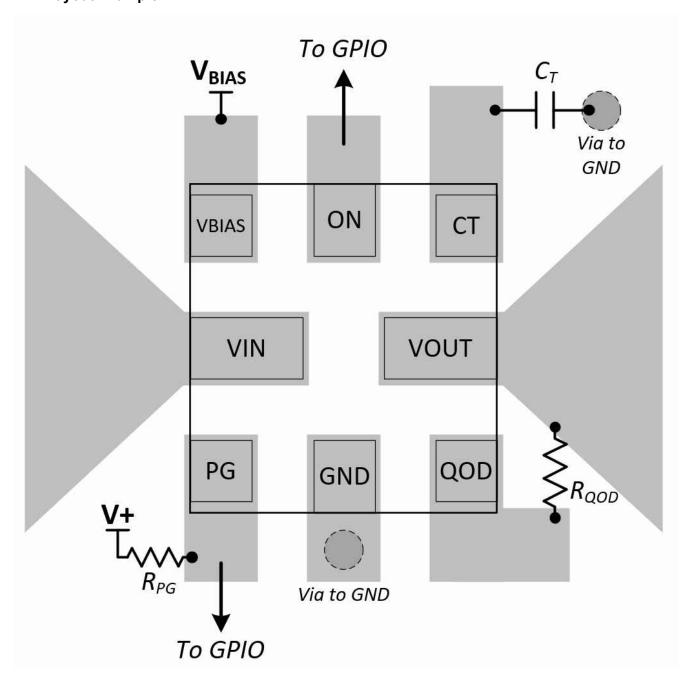


图 12-1. TPS22992x Layout Example

13 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

13.1 接收文档更新通知

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13.2 支持资源

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13.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

13.5 术语表

TI术语表

本术语表列出并解释了术语、首字母缩略词和定义。



14 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
TPS22992RXPR	ACTIVE	WQFN-HR	RXP	8	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	MC	Samples
TPS22992SRXNR	ACTIVE	WQFN-HR	RXN	8	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	MB	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

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- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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